

Publikationen aus der Technologieplattform "Leistungselektronik" der Forschungsfabrik Mikroelektronik Deutschland (2022)

- Tong R., Bengtsson O., Olsson J., Backlund A., Dancila D. (2022): Kilowatt Power Amplifier with Improved Power Back-Off Efficiency for Cyclotron Application. In: IEEE Transactions on Microwave Theory and Techniques, Vol. 70, Nr.2, pp. 1401-1409 (Article). DOI:10.1109/TMTT.2021.3134957. Link: <https://www.scopus.com/inward/record.uri?eid=2-s2.0-85122070677&doi=10.1109%2fTMTT.2021.3134957&partnerID=40&md5=441976d77e30a52285389414b8221131>
- Tsao Y.-F., Hsu H.-S., Wurfl J., Hsu H.-T. (2022): Dual-Band Power Amplifier Design at 28/38 GHz for 5G New Radio Applications. In: IEEE Access, Vol. 10, pp. 77826-77836 (Article). DOI:10.1109/ACCESS.2022.3193695. Link: <https://www.scopus.com/inward/record.uri?eid=2-s2.0-85135578442&doi=10.1109%2fACCESS.2022.3193695&partnerID=40&md5=f8c89d67e775dc9c647b56fb5b5c34a3>
- Neining P., John L., Zink M., Meder D., Kuri M., Tessmann A., Friesicke C., Mikulla M., Quay R., Zwick T. (2022): Broadband 100-W Ka-Band SSPA Based on GaN Power Amplifiers. In: IEEE Microwave and Wireless Components Letters, Vol. 32, Nr. 6, pp. 708-711 (Article). DOI:10.1109/LMWC.2022.3166563. Link: <https://www.scopus.com/inward/record.uri?eid=2-s2.0-85129394331&doi=10.1109%2fLMWC.2022.3166563&partnerID=40&md5=b43033b16fde8eb70ecb5fbdf7d84cf>
- Aksoyak I.K., Mock M., Kaynak M., Ulusoy A.C. (2022): A -Band Power Amplifier With Four-Way Combining in 0.13- μm SiGe. In: IEEE Microwave and Wireless Components Letters, Vol.32, Nr.11, pp.1343-1346 (Article). DOI:10.1109/LMWC.2022.3178933. Link: <https://www.scopus.com/inward/record.uri?eid=2-s2.0-85132734318&doi=10.1109%2fLMWC.2022.3178933&partnerID=40&md5=7660c3a7b5f789df591fe3889c4fda96>
- Mohamed E., Fischer G., Mausolf T., Ruecker H., Malignaggi A., Kahmen G. (2022): 220-320-GHz J-Band 4-Way Power Amplifier in Advanced 130-nm BiCMOS Technology. In: IEEE Microwave and Wireless Components Letters, Vol.32, Nr.11, pp.1335-1338 (Article). DOI:10.1109/LMWC.2022.3181407. Link: <https://www.scopus.com/inward/record.uri?eid=2-s2.0-85132694590&doi=10.1109%2fLMWC.2022.3181407&partnerID=40&md5=292a5293aaeb1969338b72cd2c21bca8>
- Bucher T., Grzyb J., Hillger P., Rucker H., Heinemann B., Pfeiffer U.R. (2022): A Broadband 300 GHz Power Amplifier in a 130 nm SiGe BiCMOS Technology for Communication Applications. In: IEEE Journal of Solid-State Circuits, Vol.57, Nr.7, pp.2024-2034 (Article). DOI:10.1109/JSSC.2022.3162079. Link: <https://www.scopus.com/inward/record.uri?eid=2-s2.0-85128261001&doi=10.1109%2fJSSC.2022.3162079&partnerID=40&md5=457d816518e3ab34e5e020869a1b63f2>
- Weitz N., Utzelmann S., Ditze S., Marz M. (2022): A Resonant Push-Pull DC-DC Converter with an Intrinsic Current Source Behavior for Radio Frequency Power Conversion. In: IEEE Transactions on Power Electronics, Vol. 37, Nr. 6, pp. 7001-7012 (Article). DOI:10.1109/TPEL.2022.3142431. Link: <https://www.scopus.com/inward/record.uri?eid=2-s2.0-85123316368&doi=10.1109%2fTPEL.2022.3142431&partnerID=40&md5=d5bd37ed0a919d42769fd4d0f8715cfc>

**Publikationen aus der Technologieplattform "Leistungselektronik" der Forschungsfabrik
Mikroelektronik Deutschland (2022)**

- Besendörfer S., Meissner E., Friedrich J. (2022): Statistical investigation of dislocation induced leakage current paths in AlGaIn/GaN HEMT structures on Si and the impact of growth conditions. In: Applied Physics Express, Vol. 15, Nr. 9, Art. 095502 (Article). DOI:10.35848/1882-0786/ac8639. Link: <https://www.scopus.com/inward/record.uri?eid=2-s2.0-85136001017&doi=10.35848%2f1882-0786%2fac8639&partnerID=40&md5=1dd3ac2cb3caf47d9edb78c4a67e8ad7>